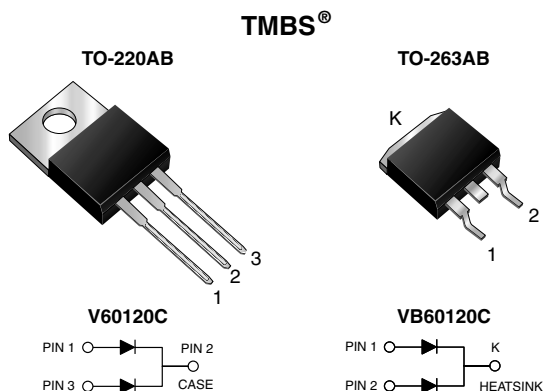




Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.41$ V at $I_F = 5$ A



FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Low thermal resistance
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 30 A
V_{RRM}	120 V
I_{FSM}	300 A
V_F at $I_F = 30$ A	0.71 V
T_J max.	150 °C

MECHANICAL DATA

Case: TO-220AB and TO-263AB

Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	V60120C	VB60120C	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	120		V
Maximum average forward rectified current (fig. 1)	per device	60		A
	per diode	30		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	300		A
Non-repetitive avalanche energy at $T_J = 25$ °C, $L = 100$ mH per diode	E_{AS}	260		mJ
Peak repetitive reverse current at $t_p = 2$ μ s, 1 kHz, $T_J = 38$ °C \pm 2 °C per diode	I_{RRM}	0.5		A
Voltage rate of change (rated V_R)	dV/dt	10 000		V/ μ s
Operating junction and storage temperature range	T_J, T_{STG}	- 40 to + 150		°C

V60120C, VB60120C

Vishay General Semiconductor



ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I _R = 1.0 mA	T _A = 25 °C	V _{BR}	120 (minimum)	-	V
Instantaneous forward voltage per diode	I _F = 5 A	T _A = 25 °C	V _F ⁽¹⁾	0.48	-	V
	I _F = 15 A			0.66	-	
	I _F = 30 A			0.88	0.95	
	I _F = 5 A	T _A = 125 °C		0.41	-	
	I _F = 15 A			0.58	-	
	I _F = 30 A			0.71	0.75	
Reverse current at rated V _R per diode	V _R = 90 V	T _A = 25 °C	I _R ⁽²⁾	14	-	μA
		T _A = 125 °C		11	-	mA
	V _R = 120 V	T _A = 25 °C		40	500	μA
		T _A = 125 °C		15	45	mA

Notes

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)				
PARAMETER	SYMBOL	V60120C	VB60120C	UNIT
Typical thermal resistance per diode	R _{θJC}	2.2	2.2	°C/W

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	V60120C-E3/4W	1.89	4W	50/tube	Tube
TO-263AB	VB60120C-E3/4W	1.38	4W	50/tube	Tube
TO-263AB	VB60120C-E3/8W	1.38	8W	800/reel	Tape and reel

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

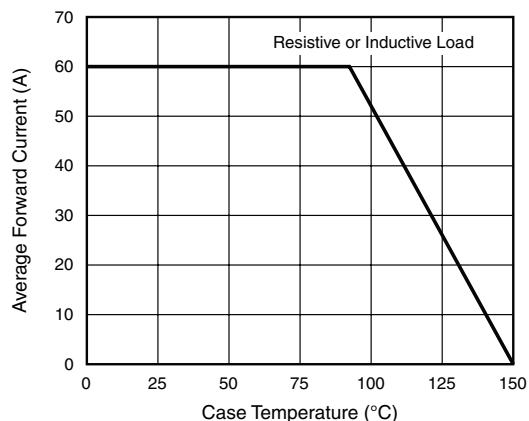


Fig. 1 - Forward Current Derating Curve

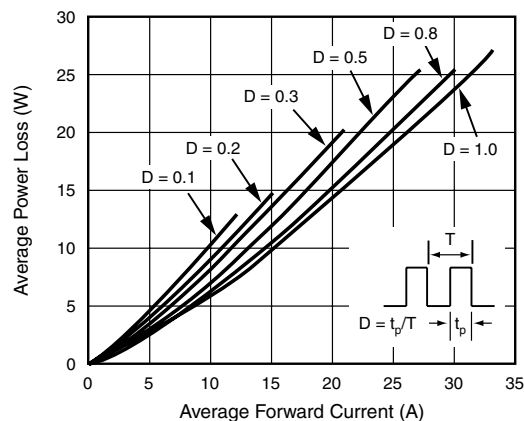


Fig. 2 - Forward Power Loss Characteristics Per Diode

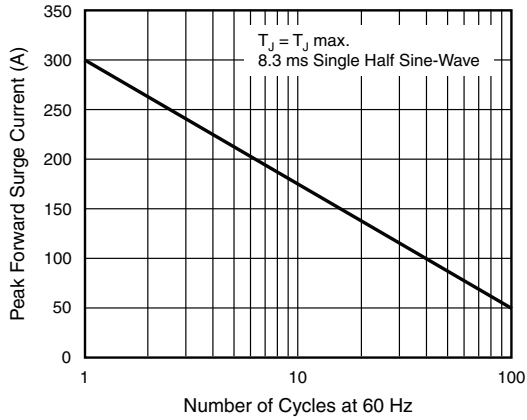


Fig. 3 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

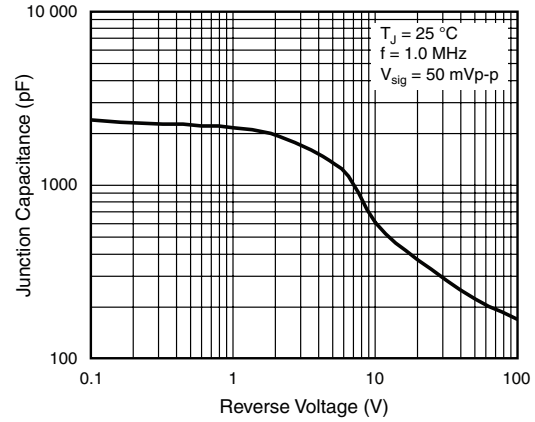


Fig. 6 - Typical Junction Capacitance Per Diode

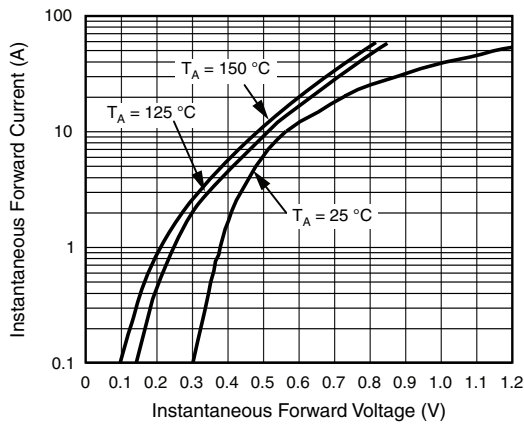


Fig. 4 - Typical Instantaneous Forward Characteristics Per Diode

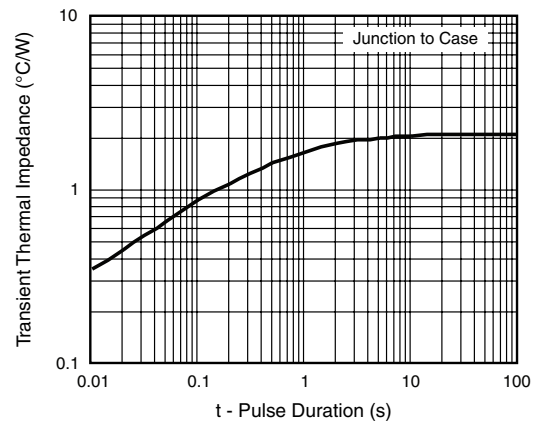


Fig. 7 - Typical Transient Thermal Impedance Per Diode

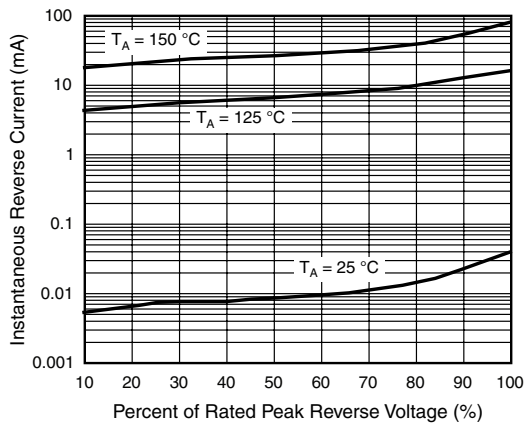


Fig. 5 - Typical Reverse Characteristics Per Diode

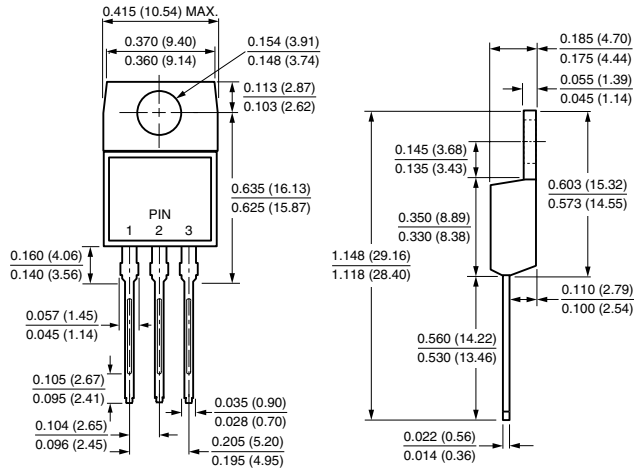
V60120C, VB60120C

Vishay General Semiconductor

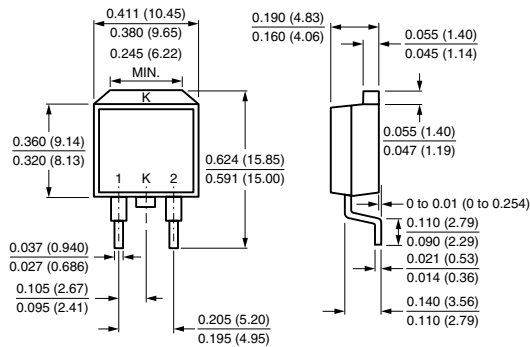


PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

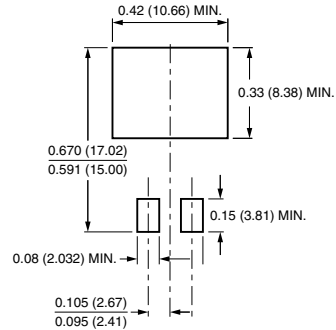
TO-220AB



TO-263AB



Mounting Pad Layout





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